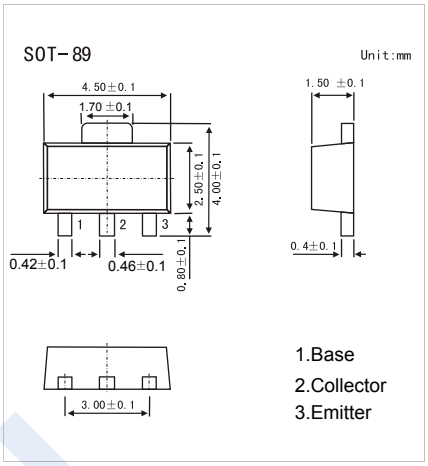
PNP Transistors

KTA1663



■ Features

- 1W (Mounted on Ceramic Substrate)
- Small Flat Package
- Comlementary to KTC4375

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-30	V
Collector - Emitter Voltage	V_{CEO}	-30	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-1.5	A
Base Current	I_B	-0.3	
Collector Power Dissipation	P_C	500	mW
		1	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -1 mA, I_E=0	-30			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, I_B=0	-30			
Emitter - base breakdown voltage	V_{EBO}	I_E= -1 mA, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1.5 A, I_B=-30mA			-2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-1.5 A, I_B=-30mA			-1.2	
Base - emitter voltage	V_{BE}	V_{CE}= -2V, I_C= -500mA			-1	
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -500mA	100		320	
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz			50	pF
Transition frequency	f_T	V_{CE}= -2V, I_C= -500mA		120		MHz

■ Classification of h_{fe}

Type	KTA1663-O	KTA1663-Y
Range	100-200	160-320
Marking	HO	HY

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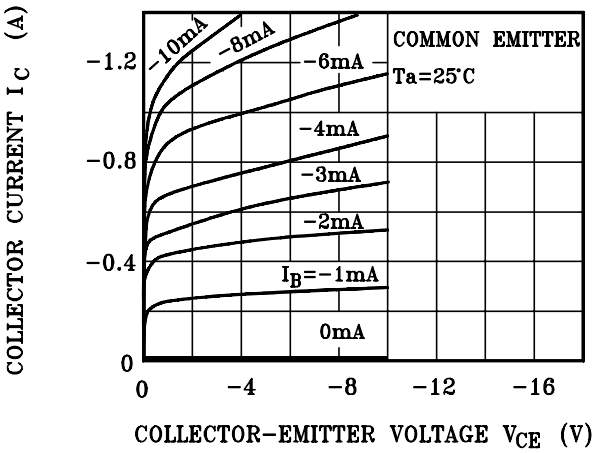
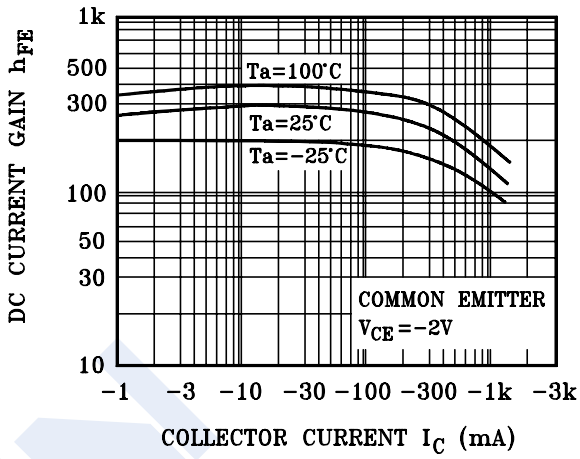
■ Typical Characterisitics

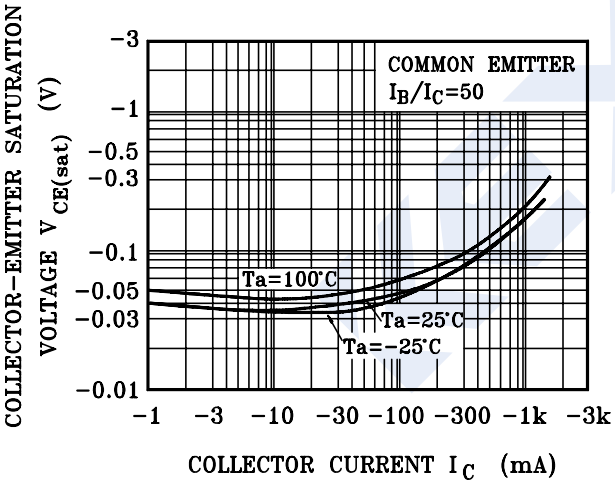
I_C – V_{CE}



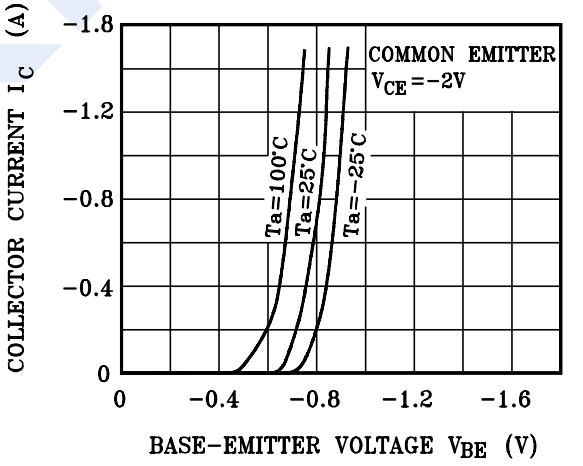
h_{FE} – I_C



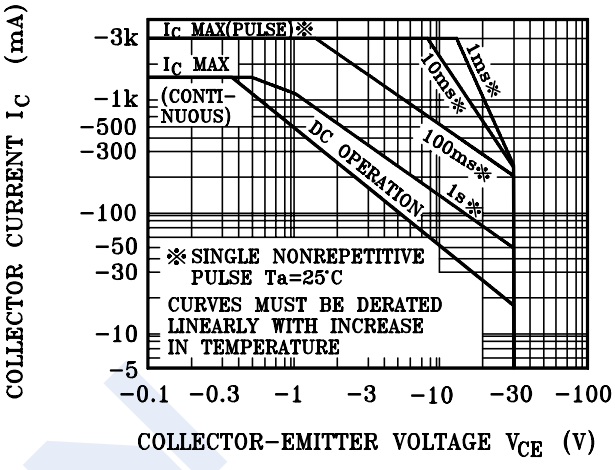
$V_{CE(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA



P_C – Ta